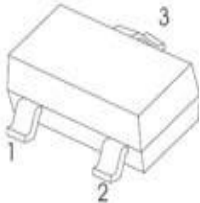
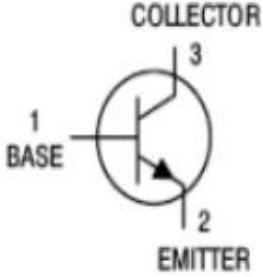


TRANSISTOR (NPN)	SOT-23 Plastic-Encapsulate Transistors		
<p><u>SOT-23</u></p>   <p>1.BASE 2.EMITTER 3.COLLECTOR</p> <p>Marking :1P</p>	<p><b>Features</b></p> <ul style="list-style-type: none"> <li>※ Complementary PNP Type available MMBT2907A</li> <li>※ Collector Current: <math>I_c=0.6A</math></li> <li>※ Epitaxial Planar die construction</li> </ul>		
<b>MAXIMUM RATINGS (Ta=25°C unless otherwise noted)</b>			
<b>Parameter</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Collector-Base Voltage	VCBO	75	V
Collector-Emitter Voltage	VCEO	40	V
Emitter-Base Voltage	VEBO	6	V
Collector Current	IC	600	mA
Collector Power Dissipation	PC	300	mW
Thermal Resistance From Junction To Ambient	R $\theta$ JA	417	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

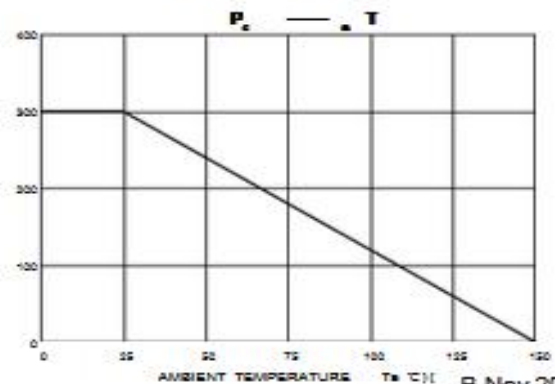
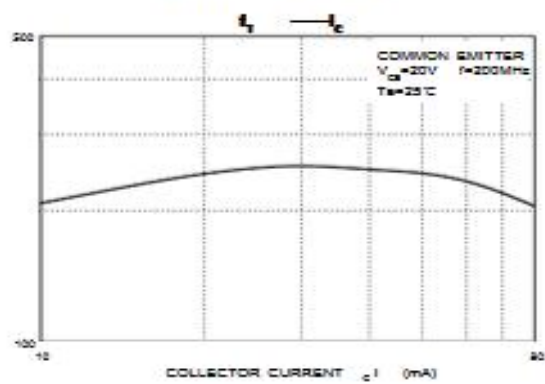
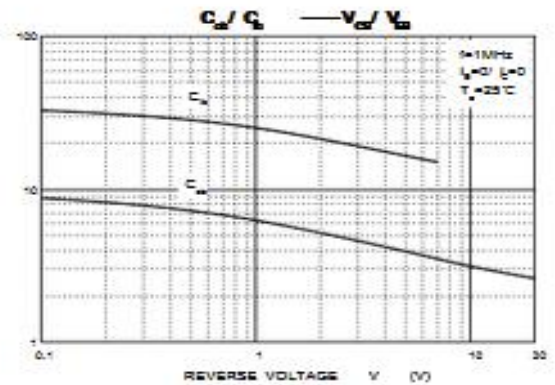
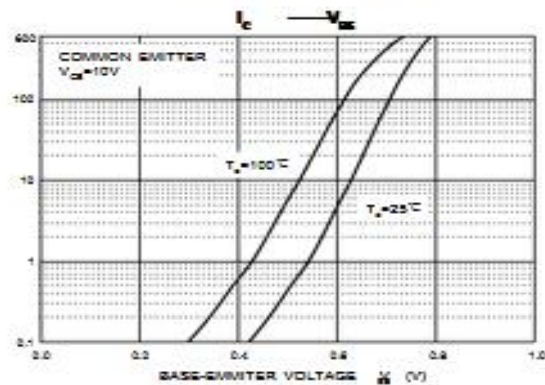
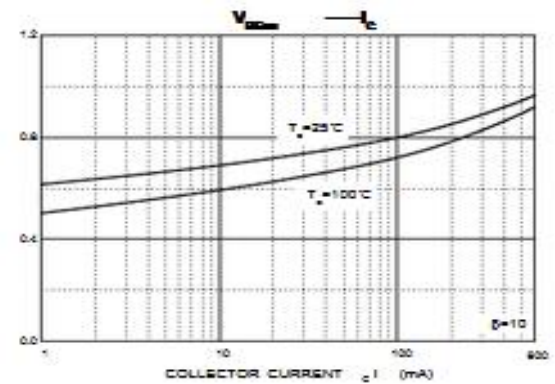
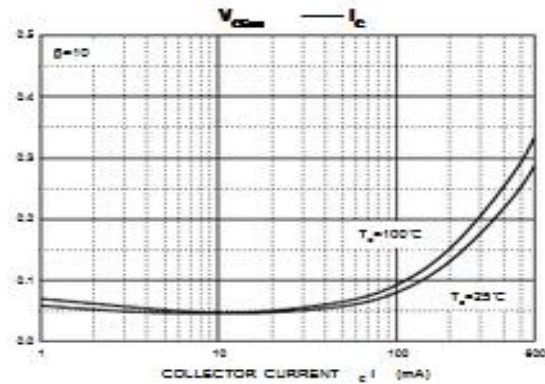
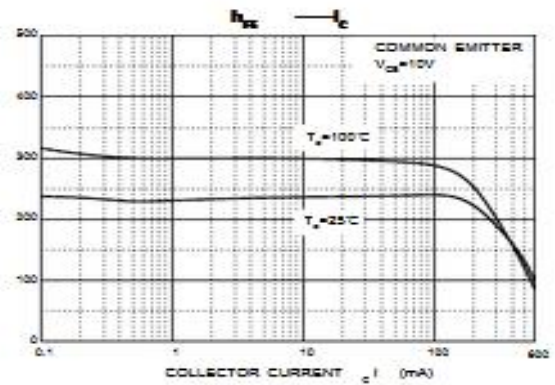
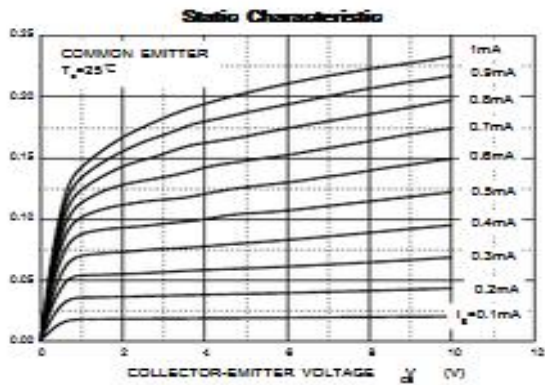
### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 10 μA, IE=0	78			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 10mA, IB=0	40			V
Emitter-base breakdown voltage	V(BR)EBO	IE=10 μA, IC=0	7			V
Collector cut-off current	ICBO	VCB=60 V , IE=0			0.01	μA
Collector cut-off current	ICEX	VCE=30V , VBE(Off)=3V			0.01	μA
Emitter cut-off current	IEBO	VEB= 3V , IC=0			0.1	μA
DC current gain	hFE	VCE=10V, IC= 150mA	100		400	
	hFE	VCE=10V, IC= 0.1mA	40			
Collector-emitter saturation voltage	VCE(sat)	IC=500 mA, IB= 50mA			1	V
Base-emitter saturation voltage	VBE(sat)	IC=500 mA, IB= 50mA			1.9	V
Transition frequency	fT	VCE=20V, IC= 20mA f=100MHz	300			MHz
Delay time	td	VCC=30V, Ic=150mA, IB1=15mA,			10	ns
Rise time	tr				25	ns
Storage time	ts	VCC=30V, Ic=150mA, IB1=15mA,			225	ns
Fall time	tf				60	ns

### CLASSIFICATION OF hFI

Rank	L	H	J
Range	120-200	200-350	300-400

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



B, Nov, 2011

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)